
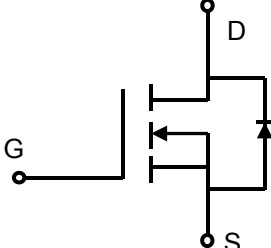



Lonten N-channel 550V, 23A, 0.14Ω LonFET™ Power MOSFET

<p>Description LonFET™ Power MOSFET is fabricated using advanced super junction technology. The resulting device has extremely low on resistance, making it especially suitable for applications which require superior power density and outstanding efficiency.</p> <p>Features</p> <ul style="list-style-type: none"> ◆ Ultra low $R_{DS(on)}$ ◆ Ultra low gate charge (typ. $Q_g = 40\text{nC}$) ◆ 100% UIS tested ◆ RoHS compliant <p>Applications</p> <ul style="list-style-type: none"> ◆ Power factor correction (PFC). ◆ Switched mode power supplies (SMPS). ◆ Uninterruptible power supply (UPS). 	<p>Product Summary</p> <table style="width: 100%; border: none;"> <tr> <td style="padding: 2px;">$V_{DS} @ T_{j,max}$</td> <td style="padding: 2px;">600V</td> </tr> <tr> <td style="padding: 2px;">$R_{DS(on),max}$</td> <td style="padding: 2px;">0.14Ω</td> </tr> <tr> <td style="padding: 2px;">I_{DM}</td> <td style="padding: 2px;">69A</td> </tr> <tr> <td style="padding: 2px;">$Q_{g,typ}$</td> <td style="padding: 2px;">40nC</td> </tr> </table> <div style="text-align: center; margin-top: 10px;">  <p style="display: flex; justify-content: space-around; font-weight: bold; font-size: small;"> TO-247 TO-220MF TO-263 </p> <div style="text-align: center; margin-top: 20px;">  <p style="margin-top: 5px;">N-Channel MOSFET</p> </div> <div style="text-align: right; margin-top: 10px;">  </div> </div>	$V_{DS} @ T_{j,max}$	600V	$R_{DS(on),max}$	0.14Ω	I_{DM}	69A	$Q_{g,typ}$	40nC
$V_{DS} @ T_{j,max}$	600V								
$R_{DS(on),max}$	0.14Ω								
I_{DM}	69A								
$Q_{g,typ}$	40nC								

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	550	V
Continuous drain current ($T_C = 25^\circ\text{C}$) ($T_C = 100^\circ\text{C}$)	I_D	23	A
		15	A
Pulsed drain current ¹⁾	I_{DM}	69	A
Gate-Source voltage	V_{GSS}	± 30	V
Avalanche energy, single pulse ²⁾	E_{AS}	600	mJ
Avalanche energy, repetitive ³⁾	E_{AR}	0.4	mJ
Avalanche current, repetitive ³⁾	I_{AR}	23	A
Power Dissipation TO-247 ($T_C = 25^\circ\text{C}$) - Derate above 25°C	P_D	205	W
		1.64	W/ $^\circ\text{C}$
Power Dissipation TO-220MF ($T_C = 25^\circ\text{C}$) - Derate above 25°C	P_D	34	W
		0.28	W/ $^\circ\text{C}$
Mounting torque To-220MF (M2.5 screws)		50	Ncm
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$
Continuous diode forward current	I_S	23	A
Diode pulse current	$I_{S,pulse}$	69	A

Thermal Characteristics TO-247/TO-263

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.61	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	60	$^{\circ}\text{C}/\text{W}$
Soldering temperature, wavesoldering only allowed at leads. (1.6mm from case for 10s)	T_{sold}	260	$^{\circ}\text{C}$

Thermal Characteristics TO-220MF

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.6	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	80	$^{\circ}\text{C}/\text{W}$
Soldering temperature, wavesoldering only allowed at leads. (1.6mm from case for 10s)	T_{sold}	260	$^{\circ}\text{C}$

Package Marking and Ordering Information

Device	Device Package	Marking	Units/Tube	Units/Reel
LSB55R140GF	TO-247	LSB55R140GF	30	
LSD55R140GF	TO-220MF	LSD55R140GF	50	
LSE55R140GF	TO-263-2L	LSE55R140GF		800

Electrical Characteristics
 $T_c = 25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{\text{GS}}=0\text{ V}, I_{\text{D}}=0.25\text{ mA}$	550	-	-	V
Gate threshold voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=0.25\text{ mA}$	3.0	3.5	4.5	V
Drain cut-off current	I_{DSS}	$V_{\text{DS}}=550\text{ V}, V_{\text{GS}}=0\text{ V},$ $T_j = 25^{\circ}\text{C}$	-	-	5	μA
			-	10	-	
Gate leakage current, Forward	I_{GSSF}	$V_{\text{GS}}=30\text{ V}, V_{\text{DS}}=0\text{ V}$	-	-	50	nA
Gate leakage current, Reverse	I_{GSSR}	$V_{\text{GS}}=-30\text{ V}, V_{\text{DS}}=0\text{ V}$	-	-	-50	nA
Drain-source on-state resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}}=10\text{ V}, I_{\text{D}}=11.5\text{ A}$ $T_j = 25^{\circ}\text{C}$	-	-	0.11	Ω
			-	0.29	-	
			-	-	-	
Gate resistance	R_{G}	$f=1\text{ MHz}, \text{open drain}$	-	4.5	-	Ω
Dynamic characteristics						
Input capacitance	C_{iSS}	$V_{\text{DS}} = 100\text{ V}, V_{\text{GS}} = 0\text{ V},$ $f = 250\text{ kHz}$	-	1730	-	pF
Output capacitance	C_{oSS}		-	76.2	-	
Reverse transfer capacitance	C_{rSS}		-	4.1	-	
Turn-on delay time	$t_{\text{d(on)}}$	$V_{\text{DD}} = 400\text{ V}, I_{\text{D}} = 11.5\text{ A}$ $R_{\text{G}} = 10\ \Omega, V_{\text{GS}}=10\text{ V}$	-	25	-	ns
Rise time	t_{r}		-	35	-	
Turn-off delay time	$t_{\text{d(off)}}$		-	97	-	
Fall time	t_{f}		-	12	-	

Gate charge characteristics						
Gate to source charge	Q_{gs}	$V_{DD}=400\text{ V}$, $I_D=11.5\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$	-	10	-	nC
Gate to drain charge	Q_{gd}		-	14	-	
Gate charge total	Q_g		-	40	-	
Gate plateau voltage	$V_{plateau}$		-	5.5	-	V
Reverse diode characteristics						
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}$, $I_F=11.5\text{ A}$	-	-	1.2	V
Reverse recovery time	t_{rr}	$V_R=50\text{ V}$, $I_F=23\text{ A}$, $dI_F/dt=100\text{ A}/\mu\text{s}$	-	171	-	ns
Reverse recovery charge	Q_{rr}		-	1.5	-	μC
Peak reverse recovery current	I_{rrm}		-	16	-	A

Notes:

- Limited by maximum junction temperature, maximum duty cycle is 0.75.
- $I_{AS} = 5\text{ A}$, $V_{DD} = 60\text{ V}$, Starting $T_J = 25^\circ\text{C}$.
- Repetitive Rating: Pulse width limited by maximum junction temperature.

Electrical Characteristics Diagrams

Figure 1. On-Region Characteristics

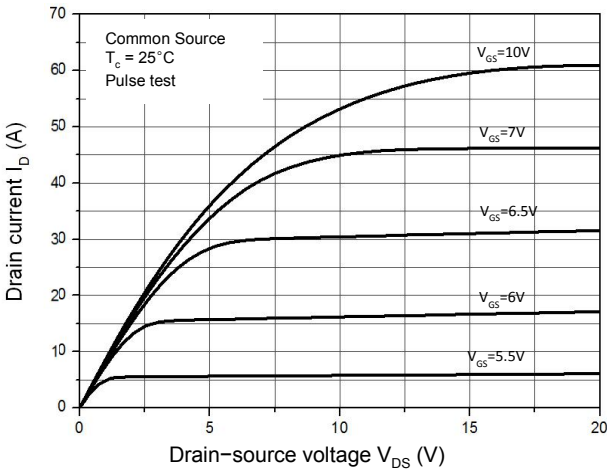


Figure 2. Transfer Characteristics

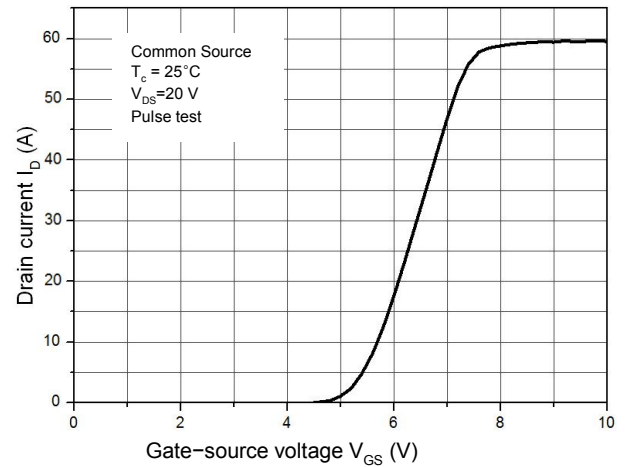


Figure 3. On-Resistance Variation vs. Drain Current

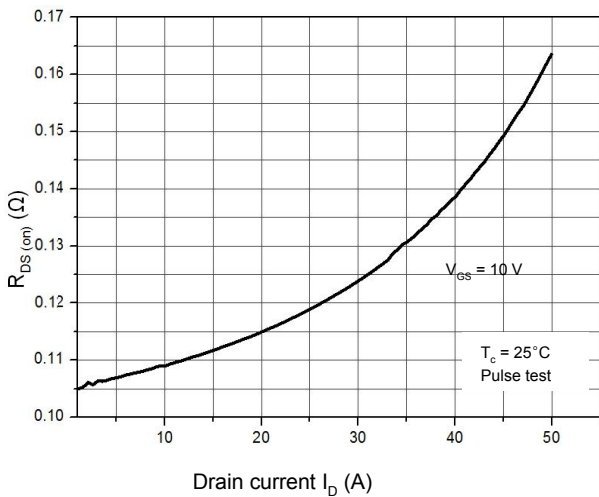


Figure 4. Threshold Voltage vs. Temperature

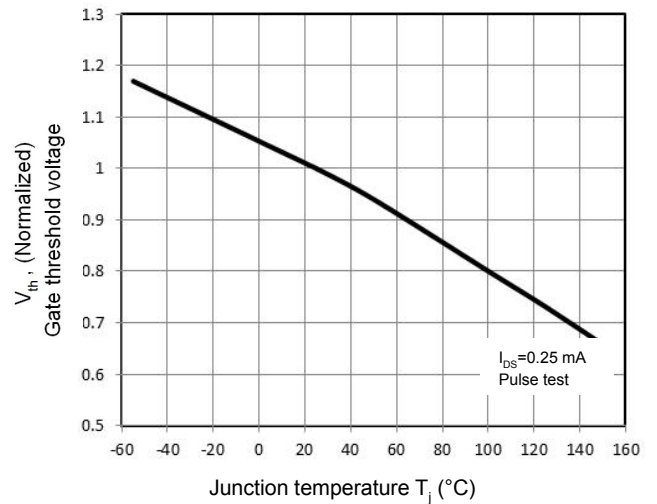


Figure 5. Breakdown Voltage vs. Temperature

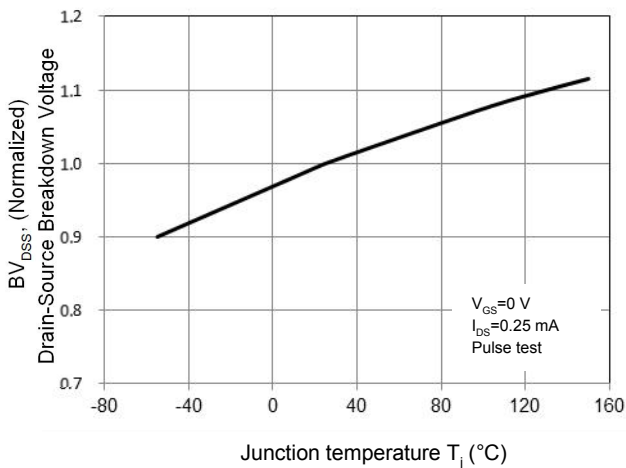


Figure 6. On-Resistance vs. Temperature

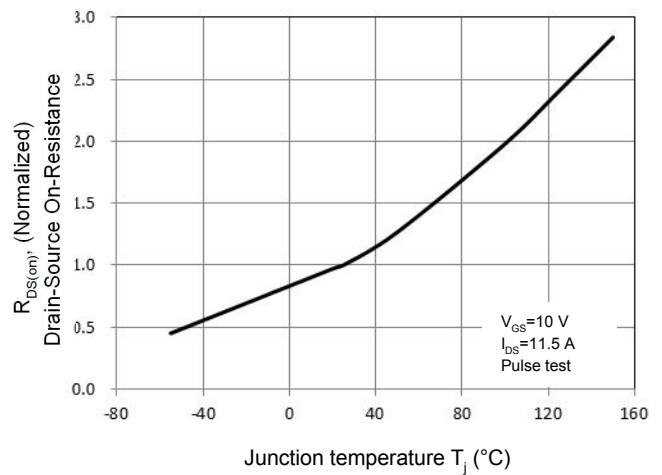


Figure 7. Capacitance Characteristics

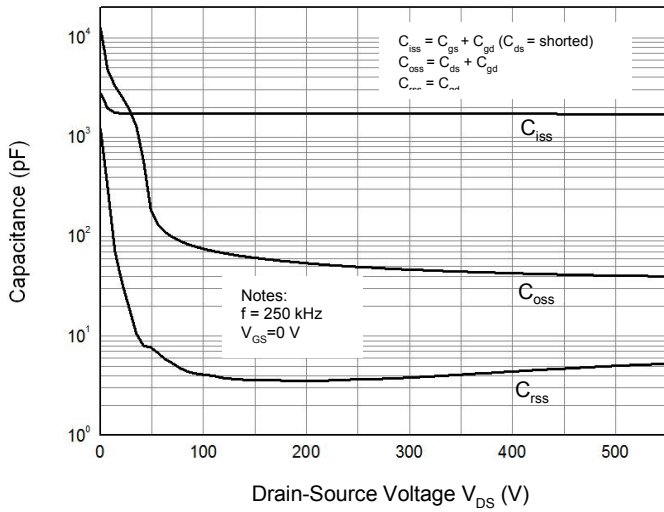


Figure 8. Gate Charge Characterist

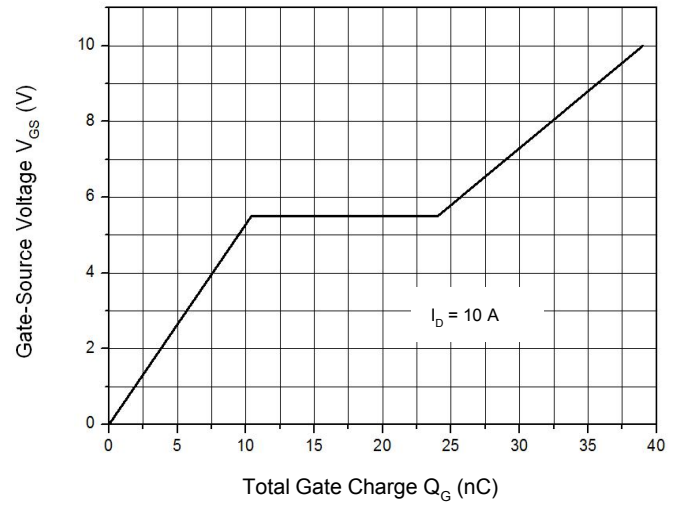


Figure 9.1 Maximum Safe Operating Area

TO-220MF

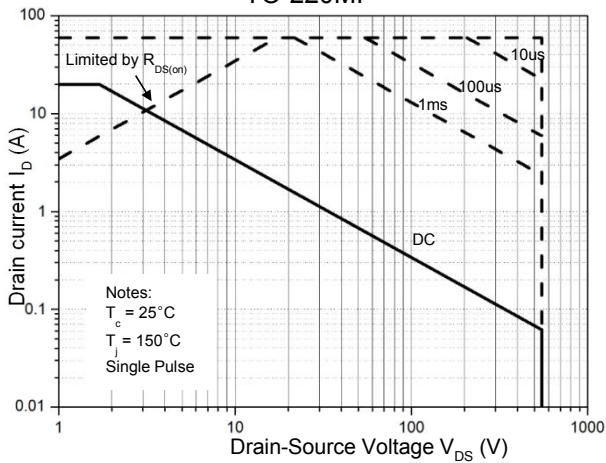


Figure 9.2 Maximum Safe Operating Area

TO-247/TO-263

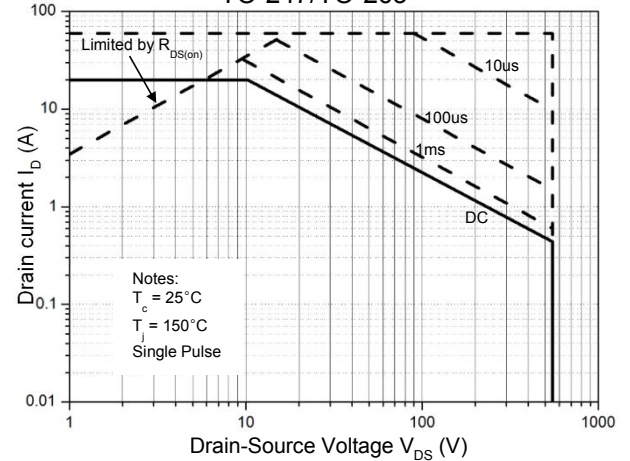


Figure 10.1 Power Dissipation vs. Temperature

TO-220MF

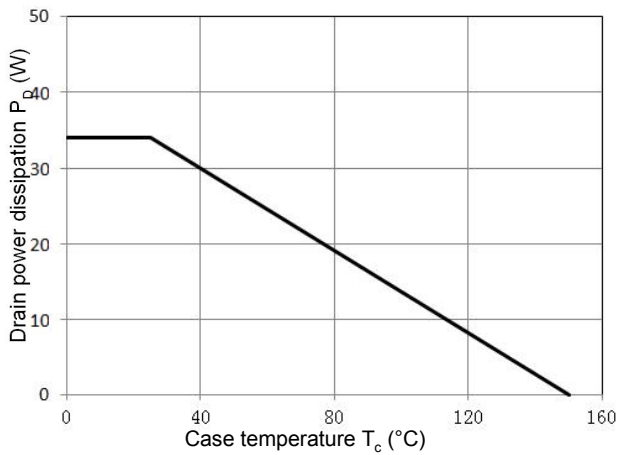


Figure 10.2 Power Dissipation vs. Temperature

TO-247/TO-263

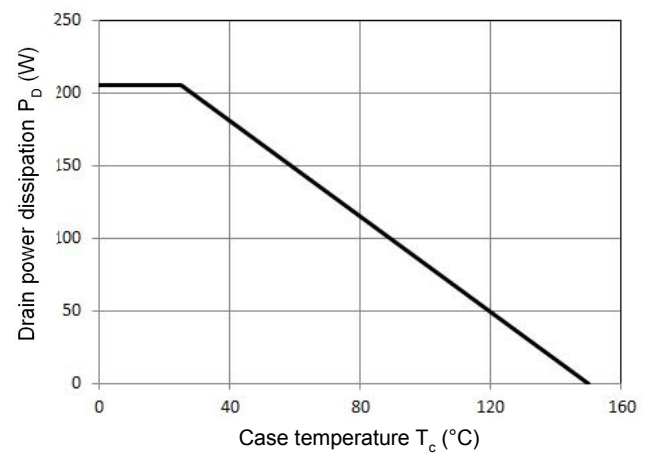


Figure 11.1 Transient Thermal Response Curve

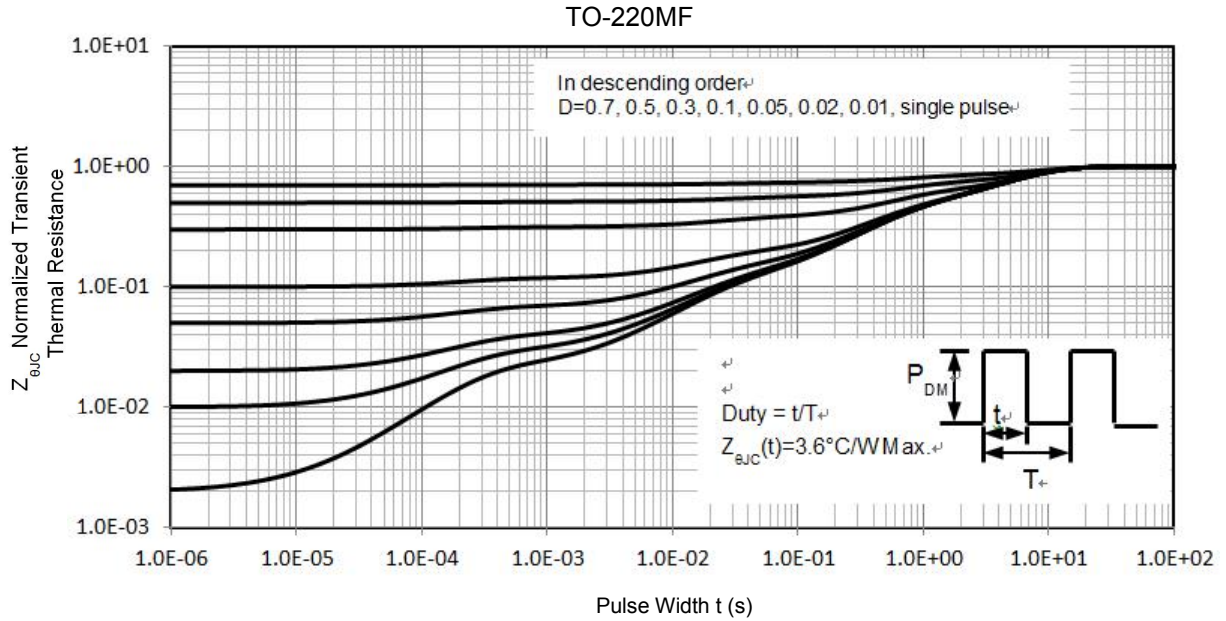
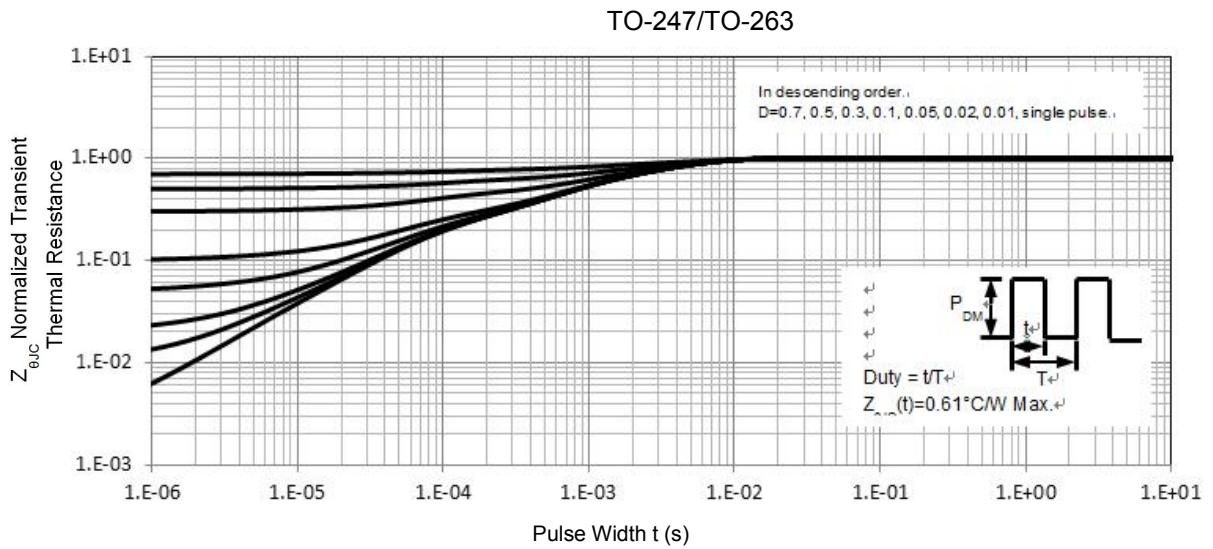
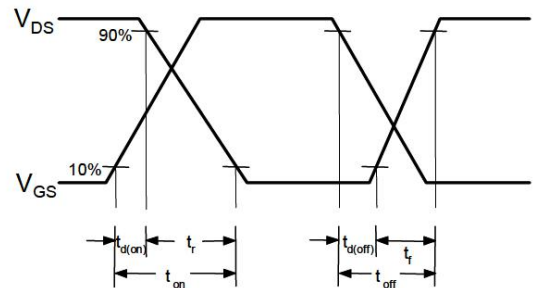
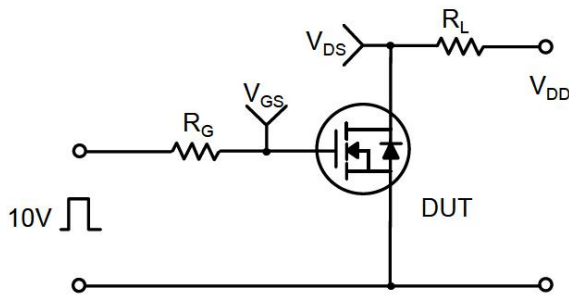
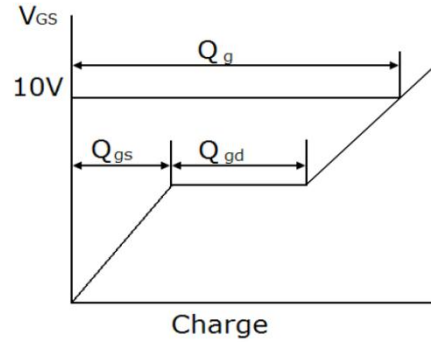
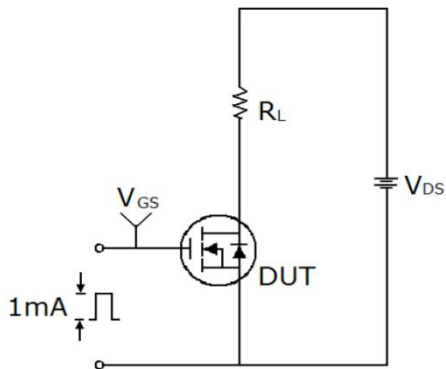


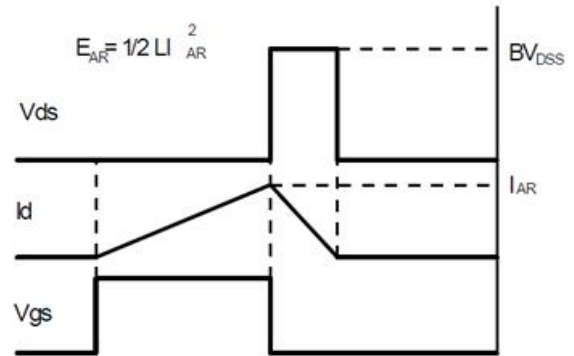
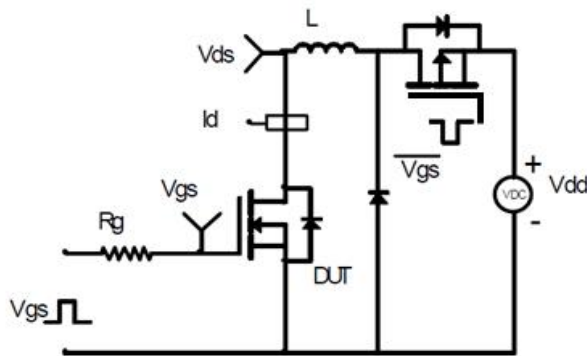
Figure 11.1 Transient Thermal Response Curve



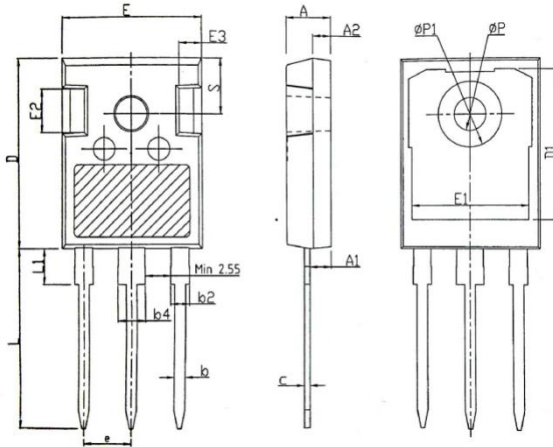
Gate Charge Test Circuit & Waveform



Unclamped Inductive Switching Test Circuit & Waveforms

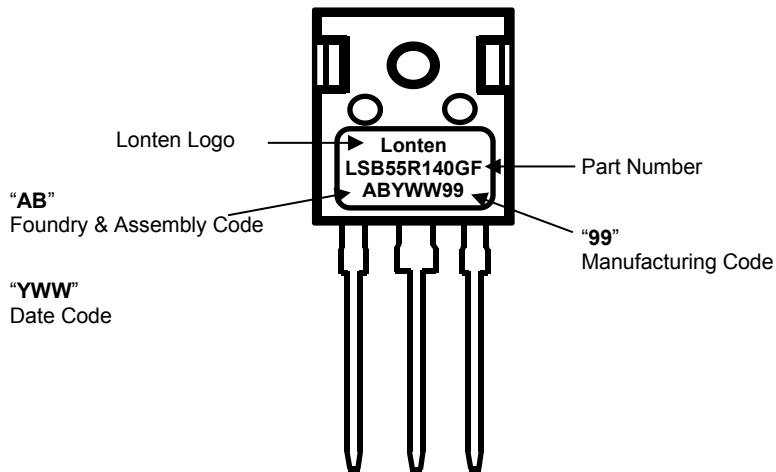


Mechanical Dimensions for TO-247

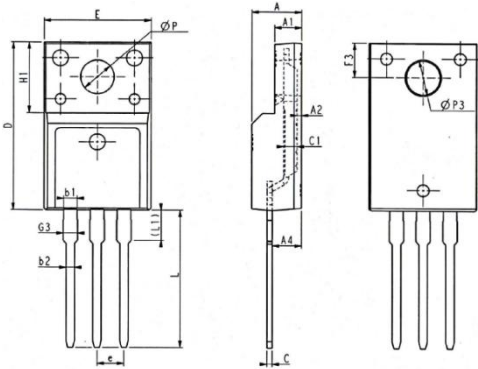


SYMBOL	mm		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.59
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.80	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	5.44BSC		
L	19.82	19.92	20.22
L1	—	—	4.30
ØP	3.40	3.60	3.80
ØP1	—	—	7.30
S	6.15BSC		

TO-247 Part Marking Information

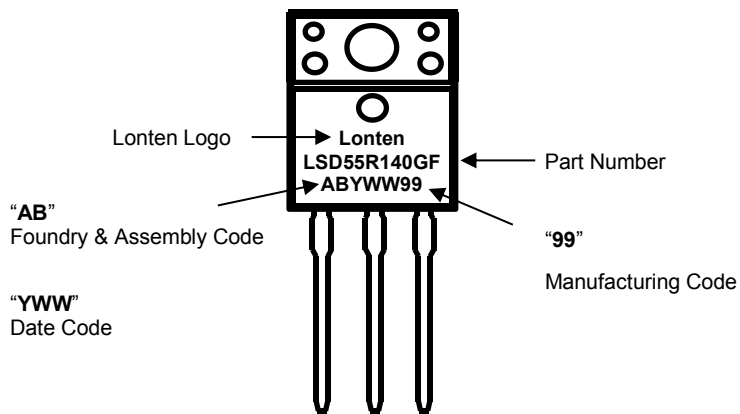


Mechanical Dimensions for TO-220MF

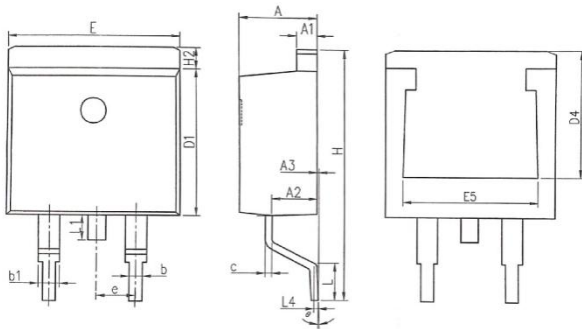


SYMBOL	COMMON DIMENSIONS					
	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
E	9.96	10.16	10.36	0.392	0.400	0.408
A	4.50	4.70	4.90	0.177	0.185	0.193
A1	2.34	2.54	2.74	0.092	0.100	0.108
A2	0.30	0.45	0.60	0.012	0.002	0.024
A4	2.65	2.76	2.96	0.104	0.109	0.117
C	0.40	0.50	0.65	0.016	0.020	0.026
C1	1.20	1.30	1.35			
D	15.57	15.87	16.17	0.613	0.625	0.637
H1	6.70REF			0.264REF		
e	2.54BSC			0.1BSC		
L	12.68	12.98	13.28	0.499	0.511	0.523
L1	2.88	3.03	3.18	0.113	0.119	0.125
ØP	3.03	3.18	3.38	0.119	0.125	0.133
ØP3	3.15	3.45	3.65	0.124	0.136	0.144
F3	3.15	3.30	3.45	0.124	0.130	0.136
G3	1.25	1.35	1.55	0.049	0.053	0.061
b1	1.18	1.28	1.43	0.046	0.050	0.056
b2	0.70	0.80	0.95	0.028	0.031	0.037

TO-220MF Part Marking Information

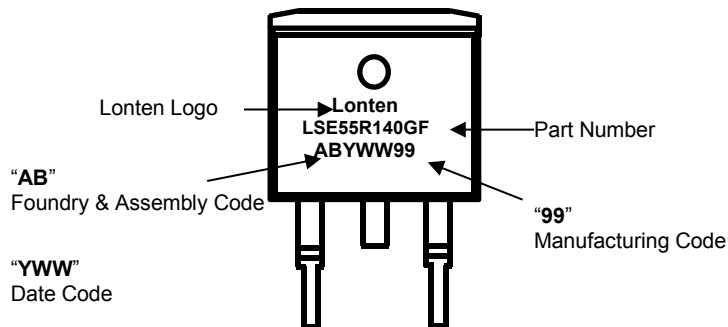


Mechanical Dimensions for TO-263



COMMON DIMENSIONS						
SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.37	4.57	4.77	0.172	0.180	0.188
A1	1.22	1.27	1.42	0.048	0.050	0.056
A2	2.49	2.89	2.89	0.098	0.114	0.114
A3	0.00	0.13	0.25	0.000	0.005	0.010
b	0.70	0.81	0.96	0.028	0.032	0.034
b1	1.17	1.27	1.47	0.046	0.050	0.058
c	0.30	0.38	0.53	0.012	0.015	0.021
D1	8.50	8.70	8.90	0.335	0.343	0.350
D4	6.60	—	—	0.260	—	—
E	9.86	10.16	10.36	0.389	0.400	0.408
E5	7.06	—	—	0.278	—	—
e	2.54 BSC			0.100 BSC		
H	14.70	15.10	15.50	0.579	0.594	0.610
H2	1.07	1.27	1.47	0.042	0.050	0.058
L	2.00	2.30	2.60	0.079	0.091	0.102
L1	1.40	1.55	1.70	0.055	0.061	0.067
L4	0.25 BSC			0.010 BSC		
θ	0°	5°	9°	0°	0.197°	0.354°

TO-263 Part Marking Information



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